

FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

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ATTY DOCKET NO.: ASC-025DV2C1

APPLICANTS: Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: Not yet assigned

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,704,302	11/03/1987	Bruel <i>et al.</i>			
	A3	4,710,788	12/01/1987	Dämbkes <i>et al.</i>			
	A4	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A5	4,990,979	02/05/1991	Otto			
	A6	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A7	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A8	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A9	5,166,084	11/24/1992	Pfiester			
	A10	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A11	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A12	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A13	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A14	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A15	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A16	5,240,876 A	08/31/1993	Gaul <i>et al.</i>			
	A17	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A18	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A19	5,285,086	02/08/1994	Fitzgerald			
	A20	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A21	5,298,452	03/29/1994	Meyerson			
	A22	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A23	5,316,958	05/31/1994	Meyerson			
	A24	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i>			
	A25	5,374,564	12/20/1994	Bruel			
	A26	5,399,522	03/21/1995	Ohuri			
	A27	5,413,679	05/09/1995	Godbey			
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	A28	5,424,243	06/13/1995	Takasaki			
	A29	5,426,069	06/20/1995	Selvakumar et al.			
	A30	5,426,316	06/20/1995	Mohammad			
	A31	5,442,205	08/15/1995	Brasen et al.			
	A32	5,461,243	10/24/1995	Ek et al.			
	A33	5,461,250	10/24/1995	Burghartz et al.			
	A34	5,462,883	10/31/1995	Dennard et al.			
	A35	5,476,813	12/19/1995	Naruse			
	A36	5,479,033	12/26/1995	Baca et al.			
	A37	5,484,664	01/16/1996	Kitahara et al.			
	A38	5,523,243	06/04/1996	Mohammad			
	A39	5,523,592	06/04/1996	Nakagawa et al.			
	A40	5,534,713	07/09/1996	Ismail et al.			
	A41	5,536,361	07/16/1996	Kondo et al.			
	A42	5,540,785	07/30/1996	Dennard et al.			
	A43	5,596,527	01/21/1997	Tomioka et al.			
	A44	5,617,351	04/01/1997	Bertin et al.			
	A45	5,630,905	05/20/1997	Lynch et al.			
	A46	5,659,187	08/19/1997	Legoues et al.			
	A47	5,683,934	11/04/1997	Candelaria			
	A48	5,698,869	12/16/1997	Yoshimi et al.			
	A49	5,714,777	02/03/1998	Ismail et al.			
	A50	5,728,623	03/17/1998	Mori			
	A51	5,739,567	04/14/1998	Wong			
	A52	5,759,898	06/02/1998	Ek et al.			
	A53	5,777,347	07/07/1998	Bartelink			
	A54	5,786,612	07/28/1998	Otani et al.			
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	A55	5,786,614	07/28/1998	Chuang et al.			
	A56	5,792,679	08/11/1998	Nakato			
	A57	5,808,344	09/15/1998	Ismail et al.			
	A58	5,847,419	12/08/1998	Imai et al.			
	A59	5,863,830	01/26/1999	Bruel et al.			
	A60	5,877,070	03/02/1999	Goesele et al.			
	A61	5,882,987	03/16/1999	Srikrishnan			
	A62	5,891,769	04/06/1999	Hong et al.			
	A63	5,906,708	05/25/1999	Robinson et al.			
	A64	5,906,951	05/25/1999	Chu et al.			
	A65	5,912,479	06/15/1999	Mori et al.			
	A66	5,943,560	08/24/1999	Chang et al.			
	A67	5,963,817	10/05/1999	Chu et al.			
	A68	5,966,622	10/12/1999	Levine et al.			
	A69	5,993,677	11/30/1999	Biasse et al.			
	A70	5,998,807	12/07/1999	Lustig et al.			
	A71	6,013,134	01/11/2000	Chu et al.			
	A72	6,013,563	01/11/2000	Henley et al.			
	A73	6,020,252	02/01/2000	Aspar et al.			
	A74	6,033,974	03/07/2000	Henley et al.			
	A75	6,033,995	03/07/2000	Muller			
	A76	6,058,044	05/02/2000	Sugiura et al.			
	A77	6,059,895	05/09/2000	Chu et al.			
	A78	6,074,919	06/13/2000	Gardner et al.			
	A79	6,096,590	08/01/2000	Chan et al.			
	A80	6,103,559	08/15/2000	Gardner et al.			
	A81	6,103,597	08/15/2000	Aspar et al.			
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	A82	6,103,599	08/15/2000	Henley et al.			
	A83	6,107,653	08/22/2000	Fitzgerald			
	A84	6,111,267	08/29/2000	Fischer et al.			
	A85	6,117,750	09/12/2000	Bensahel et al.			
	A86	6,130,453	10/10/2000	Mei, et al.			
	A87	6,133,799	10/17/2000	Favors Jr., et al.			
	A88	6,140,687	10/31/2000	Shimomura et al.			
	A89	6,143,636	11/07/2000	Forbes et al.			
	A90	6,153,495	11/28/2000	Kub et al.			
	A91	6,154,475	11/28/2000	Soref et al.			
	A92	6,160,303	12/12/2000	Fattaruso			
	A93	6,162,688	12/19/2000	Gardner et al.			
	A94	6,162,705	12/19/2000	Henley et al.			
	A95	6,184,111	02/06/2001	Henley et al.			
	A96	6,190,998 B1	02/20/2001	Bruehl et al.			
	A97	6,191,007	02/20/2001	Matsui et al.			
	A98	6,191,432	02/20/2001	Sugiyama et al.			
	A99	6,194,722	02/27/2001	Howe et al.			
	A100	6,204,529	03/20/2001	Lung, et al.			
	A101	6,207,977	03/27/2001	Augusto			
	A102	6,210,988	04/03/2001	Howe et al.			
	A103	6,218,677	04/17/2001	Broekaert			
	A104	6,225,192 B1	05/01/2001	Aspar et al.			
	A105	6,232,138	05/15/2001	Fitzgerald et al.			
	A106	6,235,567	05/22/2001	Huang			
	A107	6,242,324	06/05/2001	Kub et al.			
	A108	6,249,022	06/19/2001	Lin, et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A109	6,251,751 B1	06/26/2001	Chu et al.			
	A110	6,251,755	06/26/2001	Furukawa et al.			
	A111	6,261,929	07/17/2001	Gehrke et al.			
	A112	6,266,278	07/24/2001	Harari, et al.			
	A113	6,271,551	08/07/2001	Schmitz et al.			
	A114	6,271,726	08/07/2001	Fransis et al.			
	A115	6,290,804 B1	09/18/2001	Henley et al.			02/20/1998
	A116	6,291,321	09/18/2001	Fitzgerald			03/09/1999
	A117	6,303,468 B1	10/16/2001	Aspar et al.			10/16/2001
	A118	6,313,016	11/06/2001	Kibbel et al.			12/22/1999
	A119	6,316,301	11/13/2001	Kant			03/08/200
	A120	6,323,108	11/27/2001	Kub et al.			07/27/1999
	A121	6,326,667 B1	12/04/2001	Sugiyama et al.			09/08/2000
	A122	6,329,063	12/11/2001	Lo et al.			12/11/1998
	A123	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A124	6,339,232	01/15/2002	Takagi			09/20/1999
	A125	6,344,417 B1	02/05/2002	Usenko			08/08/2000
	A126	6,346,459 B1	02/12/2002	Usenko et al.			02/02/2000
	A127	6,350,993	02/26/2002	Chu et al.			03/12/1999
	A128	6,352,909 B1	03/05/2002	Usenko			05/26/2000
	A129	6,355,493 B1	03/12/2002	Usenko			06/30/2000
	A130	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A131	6,368,938 B1	04/09/2002	Usenko			06/07/2000
	A132	6,369,438 B1	04/09/2002	Sugiyama et al.			12/22/2000
	A133	6,372,356	04/16/2002	Thornton et al.			04/28/2000
	A134	6,372,593 B1	04/16/2002	Hattori et al.			07/19/2000
	A135	6,372,609 B1	04/16/2002	Aga et al.			10/08/1999
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	A136	6,387,829 B1	05/14/2002	Usenko et al.			04/06/2000
	A137	6,391,740 B1	05/21/2002	Cheung et al.			04/28/1999
	A138	6,399,970	06/04/2002	Kubo et al.			09/19/1997
	A139	6,403,975	06/11/2002	Brunner et al.			04/08/1997
	A140	6,407,406	06/18/2002	Tezuka			06/29/1999
	A141	6,410,371 B1	06/25/2002	Yu et al.			02/26/2001
	A142	6,425,951	07/30/2002	Chu et al.			08/06/1999
	A143	6,429,061	08/06/2002	Rim			07/26/2000
	A144	6,445,016 B1	09/03/2002	An et al.			02/28/2001
	A145	6,448,152 B1	09/10/2002	Henley et al.			07/16/2001
	A146	6,455,397 B1	09/24/2002	Belford			11/09/2000
	A147	6,458,672 B1	10/01/2002	Henley et al.			11/02/2000
	A148	6,475,072 B1	11/05/2002	Canaperi et al.			09/29/2000
	A149	6,514,836 B2	02/04/2003	Belford			06/04/2001
	A150	6,515,335 B1	02/04/2003	Christiansen et al.			01/04/2002
	A151	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A152	6,524,935 B1	02/25/2003	Canaperi et al.			09/29/2000
	A153	6,534,381 B2	03/18/2003	Cheung et al.			01/04/2000
	A154	6,555,839	04/29/2003	Fitzgerald et al.			05/16/2001
	A155	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A156	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A157	6,583,437 B2	06/24/2003	Mizuno et al.			03/19/2001
	A158	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A159	6,593,625 B2	07/15/2003	Christiansen et al.			04/03/2002
	A160	6,596,610 B1	07/22/2003	Kuwabara et al.			11/27/2000
	A161	6,602,613	08/05/2003	Fitzgerald			01/17/2001
	A162	6,603,156	08/05/2003	Rim			03/31/2001

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	A163	6,607,948 B1	08/19/2003	Sugiyama et al.			08/24/2001
	A164	6,624,047 B1	09/23/2003	Sakaguchi et al.			02/01/2000
	A165	6,624,478 B2	09/23/2003	Anderson et al.			01/30/2002
	A166	6,632,724 B2	10/14/2003	Henley et al.			01/13/2000
	A167	6,635,909 B2	10/21/2003	Clark et al.			03/19/2002
	A168	6,645,831 B1	11/11/2003	Shaheen et al.			05/07/2002
	A169	6,649,492 B2	11/18/2003	Chu et al.			02/11/2002
	A170	6,656,271 B2	12/02/2003	Yonchara et al.			12/03/1999
	A171	6,664,169 B1	12/16/2003	Iwasaki et al.			06/05/2000
	A172	6,677,183 B2	01/13/2004	Sakaguchi et al.			01/31/2002
	A173	6,680,240 B1	01/20/2004	Maszara			06/25/2002
	A174	6,680,260 B2	01/20/2004	Akiyama et al.			09/17/2002
	A175	6,690,043 B1	02/10/2004	Usuda et al.			11/22/2000
	A176	6,706,614 B1	03/16/2004	An et al.			05/15/2002
	A177	6,706,618 B2	03/16/2004	Takisawa et al.			07/29/2002
	A178	6,707,106 B1	03/16/2004	Wristers et al.			10/18/2002
	A179	6,709,903 B2	03/23/2004	Christiansen et al.			04/30/2003
	A180	6,709,909 B2	03/23/2004	Mizuno et al.			05/19/2003
	A181	6,713,326 B2	03/30/2004	Cheng et al.			03/04/2003
	A182	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
	A183	2001/0007789 A1	07/12/2001	Aspar et al.			02/26/2001
	A184	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
	A185	2002/052084	05/02/2002	Fitzgerald			05/16/2001
	A186	2002/096717	07/25/2002	Chu et al.			01/25/2001
	A187	2002/0100942	08/01/2002	Fitzgerald et al.			08/01/2002
	A188	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A189	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
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	A190	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A191	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A192	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A193	2002/0168864	11/14/2002	Cheng et al.			04/04/2002
	A194	2003/0003679	01/02/2003	Doyle et al.			06/29/2001
	A195	2003/0013305 A1	01/16/2003	Sugii et al.			6/17/2002
	A196	2003/0013323	01/16/2003	Hammond et al.			6/14/2002
	A197	2003/0025131	02/06/2003	Lee et al.			08/02/2002
	A198	2003/0034529	02/20/2003	Fitzgerald et al.			10/08/2002
	A199	2003/0057439	03/27/2003	Fitzgerald			08/09/2002
	A200	2003/0077867	04/04/2003	Fitzgerald			07/16/2001
	A201	2003/0102498	06/05/2003	Braithwaite et al.			09/24/2002
	A202	2003/0119280 A1	06/26/2003	Lee et al.			12/02/2002
	A203	2003/0127646 A1	07/10/2003	Christiansen et al.			12/18/2002
	A204	2003/0139000 A1	07/24/2003	Bedell et al.			01/23/2002
	A205	2003/0157787 A1	08/21/2003	Murthy et al.			02/21/2002
	A206	2003/0160300 A1	08/28/2003	Takenaka et al.			02/24/2003
	A207	2003/0168654 A1	09/11/2003	Cheng et al.			03/07/2003
	A208	2003/0178681 A1	09/25/2003	Clark et al.			04/02/2003
	A209	2003/0189229 A1	10/09/2003	Mouli			04/05/2002
	A210	2003/0199126 A1	10/23/2003	Chu et al.			04/23/2002
	A211	2003/0201458 A1	10/30/2003	Clark et al.			05/16/2003
	A212	2003/0203600 A1	10/30/2003	Chu et al.			06/05/2003
	A213	2003/0207127 A1	11/06/2003	Murthy et al.			05/30/2003
	A214	2003/0218189 A1	11/27/2003	Christiansen et al.			11/19/2002
	A215	2003/0219957 A1	11/27/2003	Kuwabara et al.			05/29/2003
	A216	2003/0227036 A1	12/11/2003	Sugiyama et al.			02/21/2003
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	A217	2003/0227057	12/01/2003	Lochtefeld et al.			10/04/2002
	A218	2003/0230778 A1	12/18/2003	Park et al.			01/30/2003
	A219	2003/0232467 A1	12/18/2003	Anderson et al.			05/29/2003
	A220	2004/0005740	01/01/2004	Lochtefeld et al.			06/06/2003
	A221	2004/0007724 A1	01/15/2004	Murthy et al.			07/12/2002
	A222	2004/0009649 A1	01/15/2004	Kub et al.			05/20/2003
	A223	2004/0012037 A1	01/22/2004	Venkatesan et al.			07/18/2002
	A224	2004/0012075 A1	01/22/2004	Bedell et al.			07/16/2002
	A225	2004/0014304 A1	01/22/2004	Bhattacharyya			07/18/2002
	A226	2004/0018699 A1	01/29/2004	Boyd et al.			07/24/2002
	A227	2004/0031979	02/19/2004	Lochtefeld et al.			06/06/2003
	A228	2004/0031990 A1	02/19/2004	Jin et al.			08/16/2002
	A229	2004/0041174 A1	03/04/2004	Okihara			03/21/2003
	A230	2004/0041210 A1	03/04/2004	Mouli			09/02/2003
	A231	2004/0048091 A1	03/11/2004	Sato et al.			09/04/2003
	A232	2004/0048454 A1	03/11/2004	Sakaguchi			09/04/2003
	A233	2004/0051140 A1	03/18/2004	Bhattacharyya			09/12/2002
	A234	2004/0053477 A1	03/18/2004	Ghyselen et al.			07/09/2003

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				No	No
	B2	0 514 018	11/19/1992	EP				No	Yes
	B3	0 587 520	03/16/1994	EP				No	Yes
	B4	0 683 522	11/22/1995	EP				No	Yes
	B5	0 828 296	03/11/1998	EP				No	Yes
	B6	0 829 908	03/18/1998	EP				No	Yes
	B7	0 838 858	04/29/1998	EP				No	No

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLAS S	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B8	1 020 900	07/19/2000	EP				No	Yes
	B9	1 174 928	01/23/2002	EP				No	Yes
	B10	2 342 777	04/19/2000	GB				Yes	Yes
	B11	4-307974	10/30/1992	JP				No	No
	B12	5-166724	07/03/1993	JP				No	Abstract Only
	B13	6-177046	06/24/1994	JP				No	Abstract Only
	B14	7-106446	04/21/1995	JP				No	No
	B15	7-240372	09/12/1995	JP				No	Abstract Only
	B16	10-270685	10/09/1998	JP				No	Yes
	B17	11-233744	08/27/1999	JP				No	No
	B18	2000-021783	01/21/2000	JP				No	Yes
	B19	2000-31491	01/28/2000	JP				No	No
	B20	2001319935	05/11/2000	JP				Yes	Yes
	B21	2002-076334	03/15/2002	JP				No	Yes
	B22	2002-164520	06/07/2002	JP				No	Yes
	B23	2002-289533	10/04/2002	JP				No	Yes
	B24	WO 98/59365	12/30/1998	PCT				No	Yes
	B25	WO 99/53539	10/21/1999	PCT				No	Yes
	B26	WO 00/48239	08/17/2000	PCT				No	Yes
	B27	WO 01/54202	07/26/2001	PCT				No	Yes
	B28	WO 01/99169A2	12/27/2001	PCT				No	Yes
	B29	WO 02/15244 A2	02/21/2002	PCT				No	Yes
	B30	WO 02/27783 A1	04/04/2002	PCT				No	Yes
	B31	WO 02/071495A1	09/12/2002	PCT				No	Yes

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INFORMATION DISCLOSURE STATEMENT

COPY

ATTY DOCKET NO.: ASC-025DV2C1

APPLICANTS: Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: Not yet assigned

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	B33	WO 00/54338	09/14/2000	WO				No	Yes
	B34	WO 01/022482	03/29/2001	WO				No	Yes
	B35	WO 01/93338	12/06/2001	WO				No	Yes
	B36	WO 02/13262	02/14/2002	WO				No	Yes
	B37	WO 02/47168	06/13/2002	WO				No	Yes
	B38	WO 02/071488	09/12/2002	WO				No	Yes
	B39	WO 02/071491	09/12/2002	WO				No	Yes
	B40	WO 04/006311 A2	01/15/2004	WO			07/09/2003		YES
	B41	WO 04/006326 A1	01/15/2004	WO			07/09/2003		YES
	B42	WO 04/006327 A2	01/15/2004	WO			07/09/2003		YES
	B43	WO 04/019403 A2	03/04/2004	WO			08/26/2003		YES
	B44	WO 04/019404 A2	03/04/2004	WO			08/26/2003		YES

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	C42 Ismail et al., "Modulation-doped n-type Si/SiGe with inverted interface," <u>Appl. Phys. Lett.</u> , Vol. 65, No. 10 (September 5, 1994) pp. 1248-1250.
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